

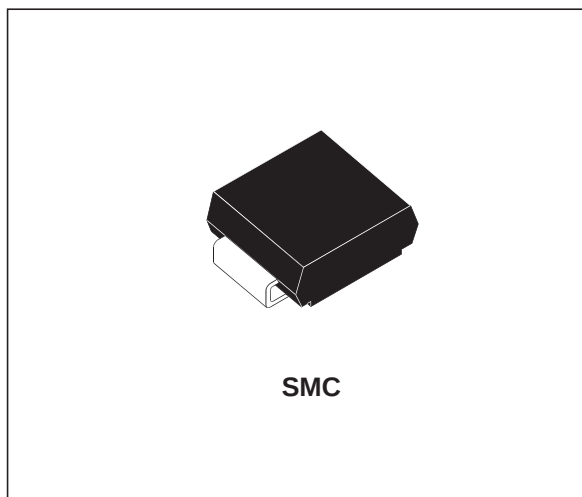
HIGH EFFICIENCY ULTRAFAST DIODE

MAIN PRODUCT CHARACTERISTICS

I_{F(AV)}	3A
V_{RRM}	200 V
T_j (max)	175 °C
V_F (max)	0.75 V
t_{rr} (max)	35 ns

FEATURES AND BENEFITS

- Very low conduction losses
- Negligible switching losses
- Low forward and reverse recovery times
- High junction temperature



DESCRIPTION

The STTH302S, which is using ST's new 200V planar technology, is specially suited for switching mode base drive & transistor circuits.

The device is also intended for use as a free wheeling diode in power supplies and other power switching applications.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V _{RRM}	Repetitive peak reverse voltage		200	V
I _{F(AV)}	Average forward current	T _I = 107°C δ = 0.5	3	A
I _{FSM}	Surge non repetitive forward current	t _p = 10 ms Sinusoidal	100	A
T _{stg}	Storage temperature range		- 65 + 175	°C
T _j	Maximum operating junction temperature		175	°C

THERMAL PARAMETERS

Symbol	Parameter	Maximum	Unit
R _{th(j-l)}	Junction to lead	20	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			3	μA
		$T_j = 125^\circ\text{C}$			4	75	
V_F^{**}	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 3\text{ A}$			0.95	V
		$T_j = 125^\circ\text{C}$	$I_F = 3\text{ A}$		0.66	0.75	

Pulse test: * $t_p = 5\text{ms}$, $\delta < 2\%$

** $t_p = 380\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 0.60 \times I_{F(AV)} + 0.05 I_{F(RMS)}^2$$

DYNAMIC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
t_{rr}	Reverse recovery time	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$ $I_{rr} = -50\text{ A}/\mu\text{s}$ $V_R = 30\text{V}$			35	ns
t_{fr}	Forward recovery time	$T_j = 25^\circ\text{C}$	$I_F = 3\text{ A}$ $di_F/dt = 50\text{ A}/\mu\text{s}$ $V_{FR} = 1.1 \times V_{Fmax}$		70		ns
V_{FP}	Forward recovery voltage	$T_j = 25^\circ\text{C}$	$I_F = 3\text{ A}$ $di_F/dt = 50\text{ A}/\mu\text{s}$		1.6		V

Fig. 1: Average forward power dissipation versus average forward current.

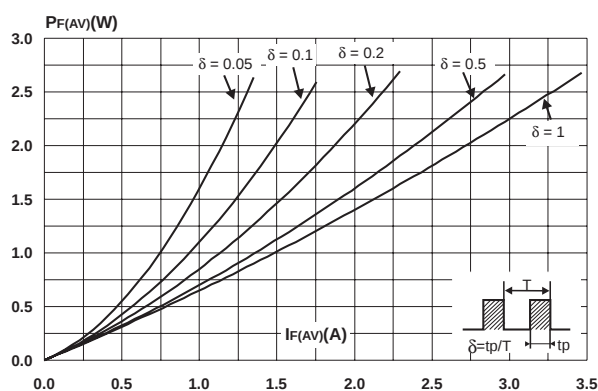


Fig. 2: Average forward current versus ambient temperature ($\delta = 0.5$).

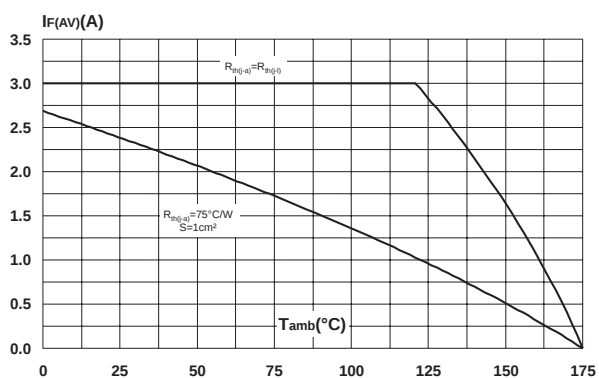


Fig. 3: Relative variation of thermal impedance junction ambient versus pulse duration (Printed circuit board epoxy FR4).

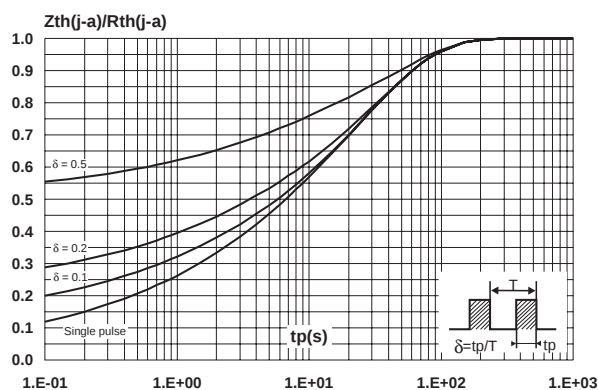


Fig. 4: Forward voltage drop versus forward current.

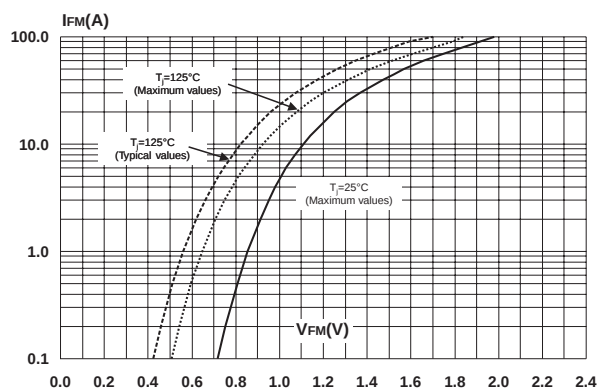


Fig. 5: Junction capacitance versus reverse voltage applied (typical values).

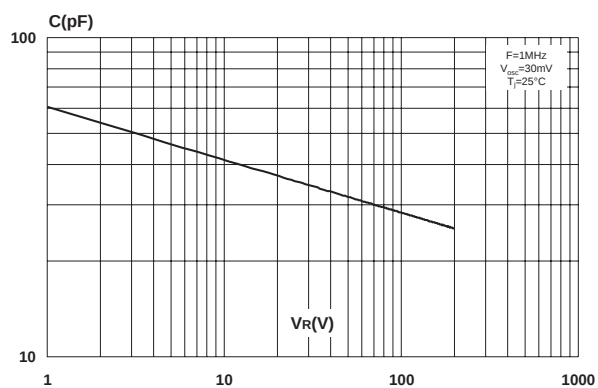


Fig. 6: Reverse recovery time versus dI_F/dt (90% confidence).

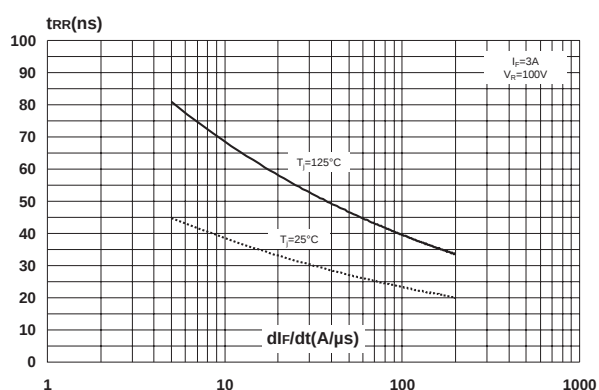


Fig. 7: Peak reverse recovery current versus di_F/dt (90% confidence).

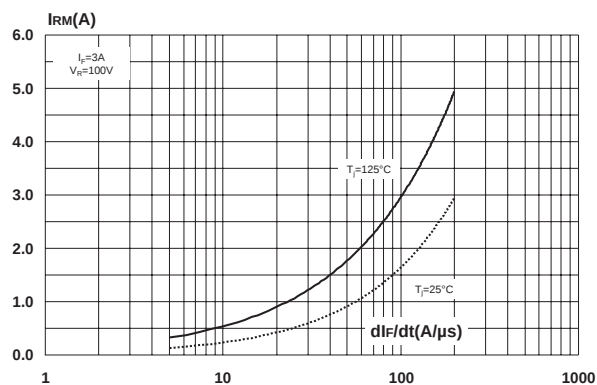


Fig. 8: Reverse recovery charges versus di_F/dt (90% confidence).

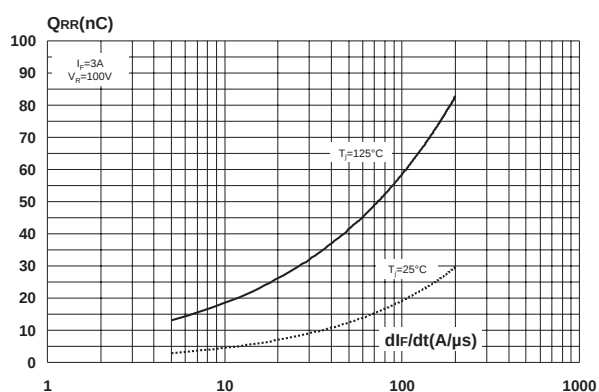


Fig. 9: Relative variations of dynamic parameters versus junction temperature.

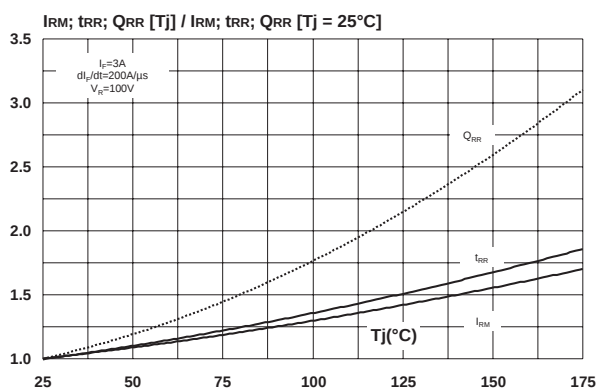
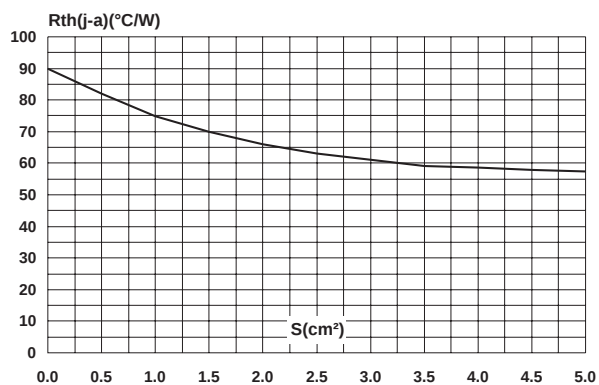


Fig. 10: Thermal resistance junction to ambient versus copper surface under each lead (epoxy FR4, $e = 35\mu m$).

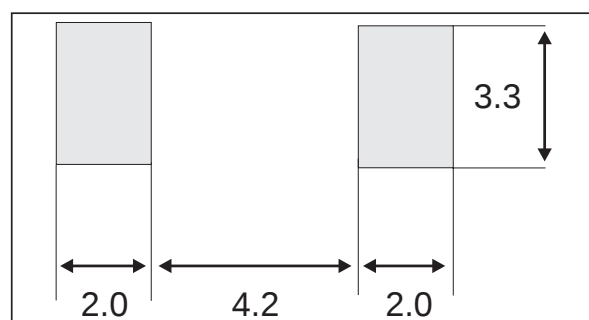


PACKAGE MECHANICAL DATA

SMC

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.075	0.096
A2	0.05	0.20	0.002	0.008
b	2.90	3.2	0.114	0.126
c	0.15	0.41	0.006	0.016
E	7.75	8.15	0.305	0.321
E1	6.60	7.15	0.260	0.281
E2	4.40	4.70	0.173	0.185
D	5.55	6.25	0.218	0.246
L	0.75	1.60	0.030	0.063

FOOTPRINT



Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH302S	U32	SMC	0.245 g	2500	Tape & reel

- Epoxy meets UL 94,V0

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На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

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